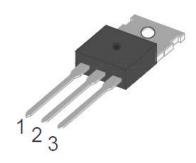
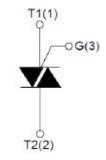




8A TRIAC

BT137-600D





TO-220 Plastic Package

For use in General Purpose Bidirectional Swiching and Phase Control Applications

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Off-State Voltage (Tj=25°C)	V _{DRM}	600	V
Repetitive Peak Reverse Voltage (Tj=25°C)	V _{RRM}	600	V
Non Repetitive Surge Peak Off-State Voltage	V _{DSM}	700	V
Non Repetitive Peak Reverse Voltage	V _{RSM}	700	V
RMS On-State Current	I _{T(RMS)}	8	А
Non Repetitive Surge Peak On-State Current (Full Cycle, f = 50MHz)	I _{TSM}	65	А
I ² t Value For Fusing (tp=10ms)	l ² t	21	A ² s
Critical Rate of Rise of On-State Current (I _G = 2 X I _{GT})	dI/dt	50	A/μs
Peak Gate Current	l _{GM}	2	А
Average Gate Power Dissipation	$P_{G(AV)}$	0.5	W
Peak Gate Power	P _{GM}	5	W
Maximum Thermal Resistance Junction to case	R _{th(j-c)}	3	°C/W

ELECTRICAL CHARACTERISTICS (Tj = 25°C unless otherwise specified)

PARAMETER	TEST CONDITION SYMBOL		QUADRANT	VALUE	UNIT	
Gate Trigger Current	$V_{D} = 12V, R_{I} = 30\Omega$	la-	I - II - III	<5	mA	
Cate Higger Current	VD=12V, INL=3032	l _{GT}	IV	<10	шА	
Gate Trigger Voltage	$V_D=12V$, $R_L=30\Omega$	V_{GT}	ALL	<1.5	V	
Off-State Gate voltage	$V_D=V_{DRM}$, $Tj=125$ °C, $R_L=3.3$ K Ω	V_{GD}	ALL	>0.2	٧	
Latching Current	I _G =1.2 X I _{GT}	I.	I - III	<15	mA	
Laterling Current	IG-1.2 X IGT	lι	II - IV	<20		
Holding Current	$I_T = 100 \text{mA}$	lμ		<10	mA	
Critical Rate of Rise of Off-State Voltage	$V_D = 2/3 V_{DRM}$, Gate Open, Tj=125°C	dV/dt		>5	V/μs	







STATIC CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
On-State Voltage	I _{TM} =10A, tp=380μs	V_{TM}	<1.65	V	
Off-State Leakage Current	V _D =V _{DRM} , Tj=25°C		<5	μА	
	V _R =V _{RRM} , Tj=25°C	I _{RRM}	<5	μΑ	
Off-State Leakage Current	V _D =V _{DRM} , Tj=125°C		<1	mA	
	V _R =V _{RRM} , Tj=125°C	I _{RRM}	<1	ША	

CHARACTERISTICS CURVES

FIG.1 Maximum power dissipation versus RMS on-state current

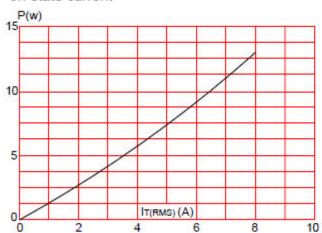


FIG.3: Surge peak on-state current versus number of cycles

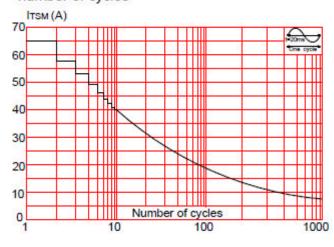


FIG.2: RMS on-state current versus case temperature

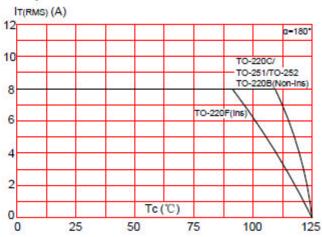


FIG.4: On-state characteristics (maximum values)

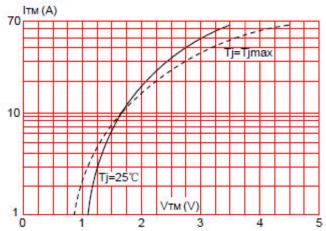






FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I²t (dI/dt < 50A/µs)

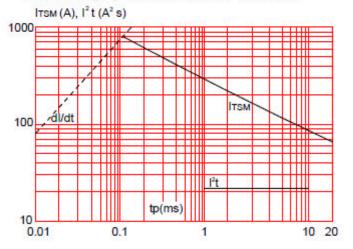


FIG.7: Relative variations of holding current versus junction temperature

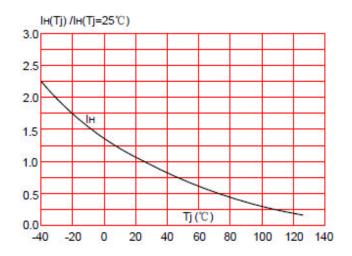


FIG.6: Relative variations of gate trigger current versus junction temperature

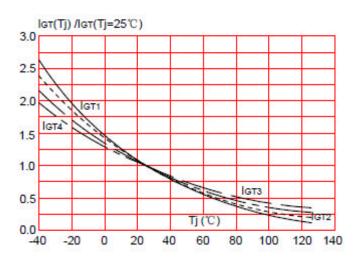
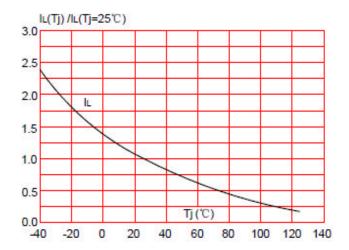


FIG.8: Relative variations of latching current versus junction temperature

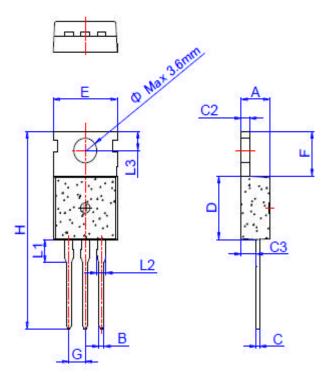








PACKAGE OUTLINE AND DIMENSION



	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.40		4.60	0.173		0.181
В	0.70		0.90	0.028		0.035
С	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
Н	28.0		29.8	1.102		1.173
L1	A 1	3.39	80	8	0.133	A.
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	







Customer Notes

Component Disposal Instructions

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

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